

10/036303  
12/28/01

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PATENT NUMBER and  
ISSUE DATE

U.S. UTILITY Patent Application

505/503

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10036303	12/28/2001	257	5	2811	

\*\*APPLICANTS: Hawley Frank; Wang Daniel;

\*\*CONTINUING DATA VERIFIED:

THIS APPLICATION IS A DIV OF 09/741,949 12/20/2000

\*\* FOREIGN APPLICATIONS VERIFIED:

PG-PUB	DO NOT PUBLISH <input checked="" type="checkbox"/>	RESCIND <input type="checkbox"/>
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no		ATTORNEY DOCKET NO
35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no		ACT-307DVA
Verified and Acknowledged Examiners's initials		
TITLE : Method for fabricating a MOS transistor having improved total radiation-induced leakage current		

U.S. DEPT. OF COMMERCE / PAT & TM-PTO-436L (Rev. 12-94)

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NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Total Claims	Print Claim for O.G.
Assistant Examiner		DRAWING	
		Sheets Drwg.	Figs. Drwg.
Primary Examiner		Print Fig.	
PREPARED FOR ISSUE		Application Examiner	
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DISCLAIMER

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☐ CD-ROM  
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